



**TO-220BK Plastic-Encapsulate Thyristors**

**CR825B** Standard SCRs

**MAIN CHARACTERISTICS**

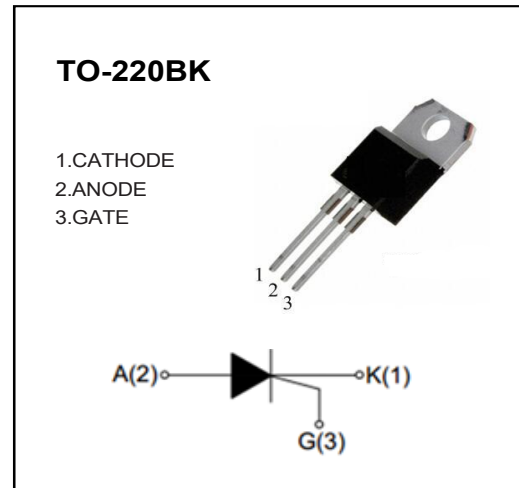
$I_{T(AV)}$	<b>16A</b>
$V_{DRM}/V_{RRM}$	<b>800V</b>
$V_{TM}$	<b>1.6V</b>

**FEATURES**

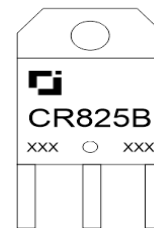
- PNP 4-layer Structure SCRs
- Mesa Glass Passivated Technology
- Multi Layers Metal Electrodes

**APPLICATIONS**

- LED Controller
- Motorcycle Voltage Regulator
- Hair Straightener



**MARKING**



CR825B:Part Number  
XXX:Internal Code

**ABSOLUTE RATINGS (  $T_a=25^\circ\text{C}$  unless otherwise noted )**

Symbol	Parameter	Test condition	Value	Unit
$V_{DRM}/V_{RRM}$	Repetitive peak off-state voltage	$T_j=25^\circ\text{C}$	800	V
$I_{T(AV)}$	Average on-state current	TO-220BK( $T_c \leq 100^\circ\text{C}$ )	16	A
$I_{T(RMS)}$	RMS on-state current	TO-220BK( $T_c \leq 100^\circ\text{C}$ ), Fig. 1,2	25	A
$I_{TSM}$	Non repetitive surge peak on-state current	Full sine wave , $T_j(\text{init})=25^\circ\text{C}$ , $t_p=20\text{ms}$ ; Fig. 3,5	300	A
$I^2t$	$I^2t$ value	$t_p=10\text{ms}$	450	$\text{A}^2\text{s}$
$di_T/dt$	Critical rate of rise of on-state current	$I_G=2 \cdot I_{GT}$ , $t_r \leq 10\text{ns}$ , $F=120\text{Hz}$ , $T_j=125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
$I_{GM}$	Peak gate current	$t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average gate power	$T_j=125^\circ\text{C}$	1	W
$T_{STG}$	Storage temperature		-40~+150	°C
$T_j$	Operating junction temperature		-40~+125	

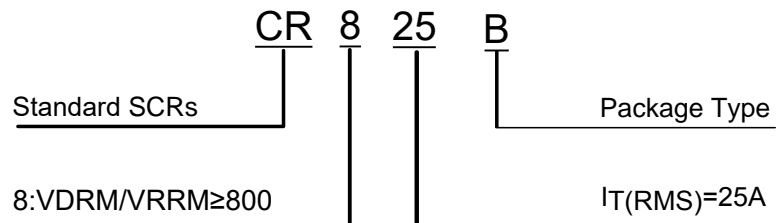
## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test condition	Value			Unit
			Min	Nom	Max	
I <sub>GT</sub>	Gate trigger current	V <sub>D</sub> =12V, R <sub>L</sub> =33Ω, T <sub>j</sub> =25°C, Fig. 6	2	-	30	mA
V <sub>GT</sub>	Gate trigger voltage	V <sub>D</sub> =12V, R <sub>L</sub> =33Ω, T <sub>j</sub> =25°C	-	-	1.0	V
V <sub>GD</sub>	Non-triggering gate voltage	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =3.3kΩ, T <sub>j</sub> =125°C	0.2	-	-	V
I <sub>H</sub>	Holding current	I <sub>T</sub> =500mA, T <sub>j</sub> =25°C,	-	-	50	mA
I <sub>L</sub>	Latching current	I <sub>G</sub> =1.2I <sub>GT</sub> , T <sub>j</sub> =25°C,	-	-	70	mA
dV <sub>D</sub> /dt	Critical rate of rise of off-state	V <sub>D</sub> =67%V <sub>DRM</sub> , Gate OPEN, T <sub>j</sub> =125°C	500	-	-	V/μs
V <sub>TM</sub>	On-state Voltage	I <sub>TM</sub> =50A, Fig. 4	-	-	1.6	V
I <sub>DRM</sub> / I <sub>RRM</sub>	Repetitive peak off-state current	V <sub>D</sub> =V <sub>DRM</sub> /V <sub>RRM</sub> , T <sub>j</sub> =25°C	-	-	5	μA
		V <sub>D</sub> =V <sub>DRM</sub> /V <sub>RRM</sub> , T <sub>j</sub> =125°C	-	-	2	mA

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th</sub> (j-c)	Junction to case (AC)	TO-220BK	1.0 °C/W
R <sub>th</sub> (j-a)	Junction to ambient	TO-220BK	60 °C/W

## PART NUMBER



# CHARACTERISTICS CURVES

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

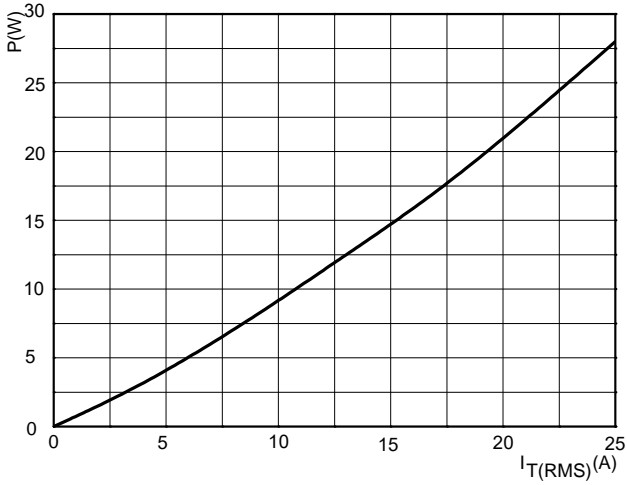


FIG.2: RMS on-state current versus case temperature (full cycle)

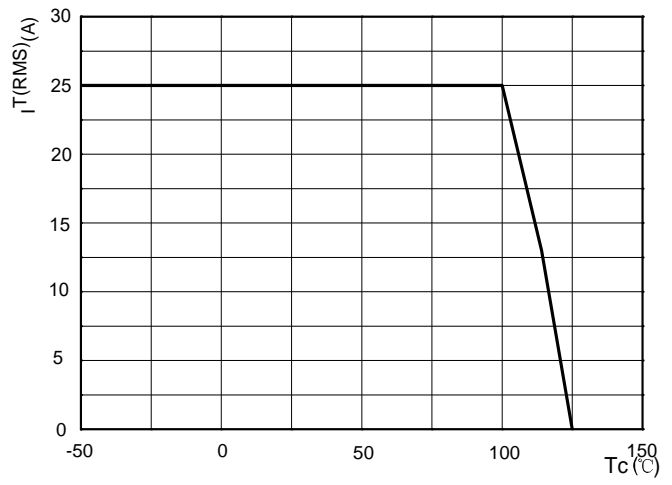


FIG.3: Surge peak on-state current versus number of cycles

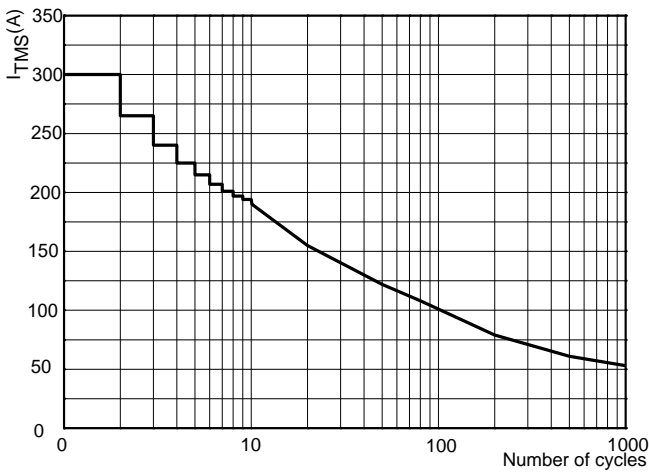


FIG.4: On-state characteristics (maximum values)

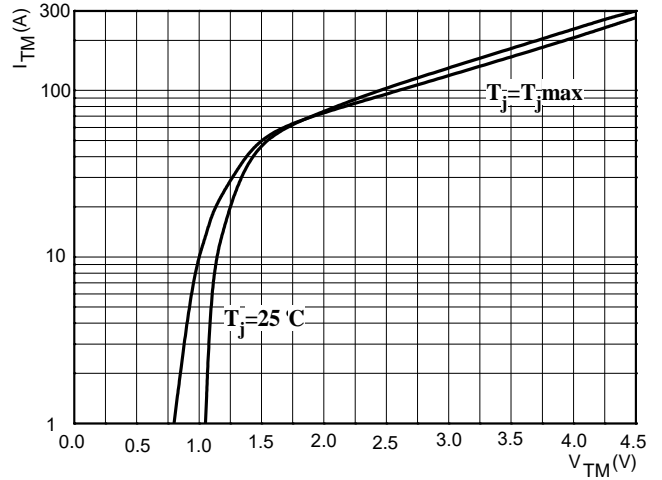


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10ms$

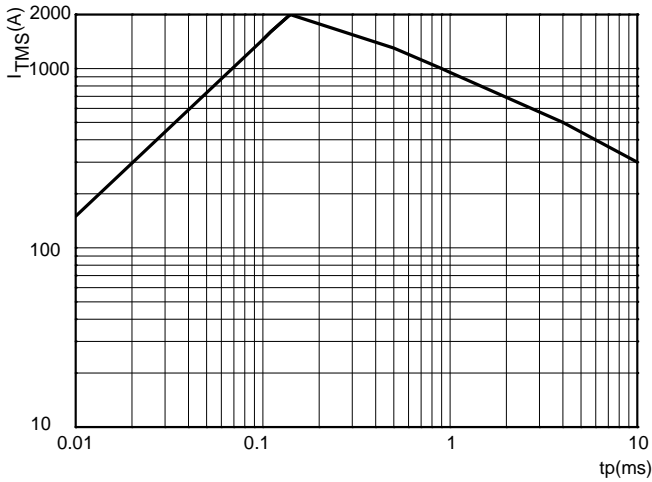
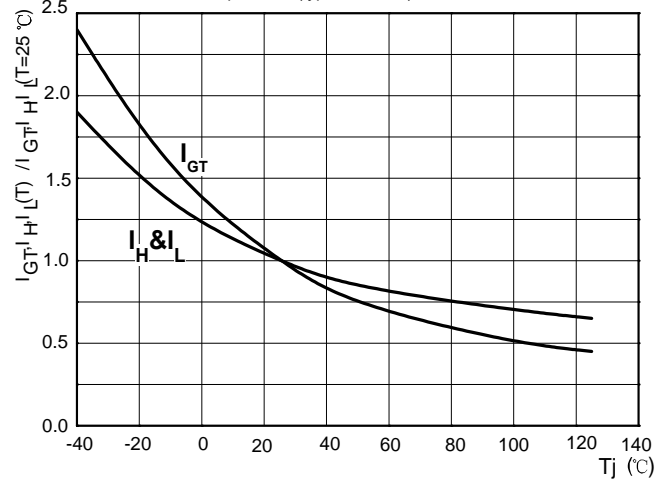
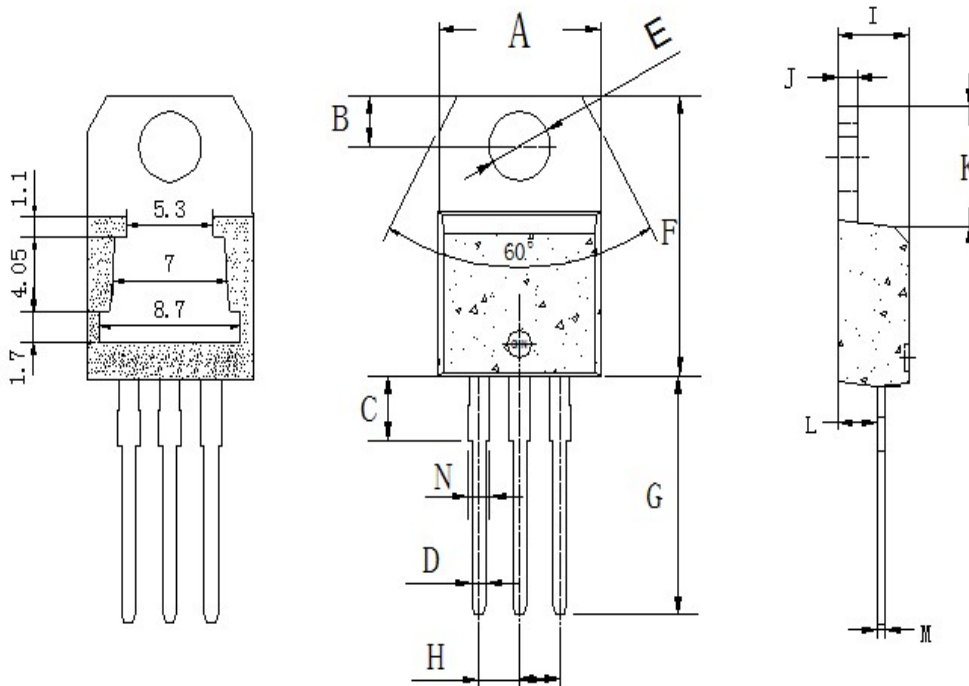


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



# TO-220BK PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.8	10.4	0.385	0.409
B	2.65	3.1	0.104	0.122
C	2.8	4.2	0.110	0.165
D	0.7	0.92	0.027	0.036
E	3.75	3.95	0.147	0.155
F	14.8	16.1	0.582	0.633
G	13.05	13.6	0.513	0.535
H	2.4	2.7	0.094	0.106
I	4.38	4.61	0.172	0.181
J	1.15	1.36	0.045	0.053
K	5.85	6.82	0.230	0.268
L	2.35	2.75	0.092	0.108
M	0.35	0.65	0.013	0.025
N	1.18	1.42	0.046	0.055

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